

**Notice of References Cited**

Application/Control No.

09/648,111

Applicant(s)/Patent Under

Reexamination

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Examiner

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Art Unit

2815

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	B	US-5968847-a	10-1999	Ye et al.	437	228
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**NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
 Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.